

# IRL640STRLPBF-VB Datasheet

## N-Channel 200 V (D-S) 175 °C MOSFET

### PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) |
|--------------|---------------------------|-----------|
| 200          | 0.048 at $V_{GS} = 10$ V  | 40        |
|              | 0.060 at $V_{GS} = 6.5$ V | 35        |

TO-263



### FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- PWM Optimized for Fast Switching
- Compliant to RoHS Directive 2002/95/EC


**RoHS**  
 COMPLIANT

### APPLICATIONS

- Isolated DC/DC Converters
- Primary-Side Switch



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

| Parameter                                        | Symbol         | Limit            | Unit |
|--------------------------------------------------|----------------|------------------|------|
| Drain-Source Voltage                             | $V_{DS}$       | 200              | V    |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 20$         |      |
| Continuous Drain Current ( $T_J = 175$ °C)       | $I_D$          | 40               | A    |
|                                                  |                | 25               |      |
| Pulsed Drain Current                             | $I_{DM}$       | 80               |      |
| Avalanche Current                                | $I_{AR}$       | 20               |      |
| Repetitive Avalanche Energy <sup>a</sup>         | $E_{AR}$       | 16.2             | mJ   |
| Maximum Power Dissipation <sup>a</sup>           | $P_D$          | 200 <sup>b</sup> | W    |
|                                                  |                | 4.5              |      |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$ | - 55 to 175      | °C   |

### THERMAL RESISTANCE RATINGS

| Parameter                | Symbol     | Limit | Unit |
|--------------------------|------------|-------|------|
| Junction-to-Ambient      | $R_{thJA}$ | 40    | °C/W |
| Junction-to-Case (Drain) | $R_{thJC}$ | 1     |      |

Notes:

a. Duty cycle  $\leq 1$  %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR-4 material).

| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)                      |                      |                                                                                                                         |       |       |       |      |
|--------------------------------------------------------------------------------------|----------------------|-------------------------------------------------------------------------------------------------------------------------|-------|-------|-------|------|
| Parameter                                                                            | Symbol               | Test Conditions                                                                                                         | Min . | Typ.  | Max.  | Unit |
| Static                                                                               |                      |                                                                                                                         |       |       |       |      |
| Drain-Source Breakdown Voltage                                                       | V <sub>DS</sub>      | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                          | 200   |       |       | V    |
| Gate-Threshold Voltage                                                               | V <sub>GS(th)</sub>  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                             | 2     |       | 4     |      |
| Gate-Body Leakage                                                                    | I <sub>GSS</sub>     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                         |       |       | ± 100 | nA   |
| Zero Gate Voltage Drain Current                                                      | I <sub>DSS</sub>     | V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V                                                                          |       |       | 1     | μA   |
|                                                                                      |                      | V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C                                                 |       |       | 50    |      |
|                                                                                      |                      | V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C                                                 |       |       | 250   |      |
| On-State Drain Current <sup>a</sup>                                                  | I <sub>D(on)</sub>   | V <sub>DS</sub> ≥ 15 V, V <sub>GS</sub> = 10 V                                                                          | 60    |       |       | A    |
| Drain-Source On-State Resistance <sup>a</sup>                                        | R <sub>DS(on)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A                                                                           |       | 0.048 |       | Ω    |
|                                                                                      |                      | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C                                                  |       | 0.150 |       |      |
|                                                                                      |                      | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C                                                  |       | 0.180 |       |      |
| Drain-Source on State Resistance                                                     |                      | V <sub>GS</sub> = 6.5 V, I <sub>D</sub> = 15 A                                                                          |       | 0.060 |       |      |
| Forward Transconductance <sup>a</sup>                                                | g <sub>fs</sub>      | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A                                                                           | 15    |       |       | S    |
| Dynamic <sup>b</sup>                                                                 |                      |                                                                                                                         |       |       |       |      |
| Input Capacitance                                                                    | C <sub>iss</sub>     | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz                                                                |       | 2820  |       | pF   |
| Output Capacitance                                                                   | C <sub>oss</sub>     |                                                                                                                         |       | 300   |       |      |
| Reverse Transfer Capacitance                                                         | C <sub>rss</sub>     |                                                                                                                         |       | 120   |       |      |
| Total Gate Charge <sup>c</sup>                                                       | Q <sub>g</sub>       | V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A                                                  |       | 35    |       | nC   |
| Gate-Source Charge <sup>c</sup>                                                      | Q <sub>gs</sub>      |                                                                                                                         |       | 11    |       |      |
| Gate-Drain Charge <sup>c</sup>                                                       | Q <sub>gd</sub>      |                                                                                                                         |       | 14    |       |      |
| Gate Resistance                                                                      | R <sub>G</sub>       |                                                                                                                         |       | 2     |       | Ω    |
| Turn-On Delay Time <sup>c</sup>                                                      | t <sub>d(on)</sub>   | V <sub>DD</sub> = 100 V, R <sub>L</sub> = 5 Ω<br>I <sub>D</sub> ≅ 20 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 2.5 Ω |       | 15    | 25    | ns   |
| Rise Time <sup>c</sup>                                                               | t <sub>r</sub>       |                                                                                                                         |       | 35    | 55    |      |
| Turn-Off Delay Time <sup>c</sup>                                                     | t <sub>d(off)</sub>  |                                                                                                                         |       | 40    | 60    |      |
| Fall Time <sup>c</sup>                                                               | t <sub>f</sub>       |                                                                                                                         |       | 30    | 45    |      |
| Source-Drain Diode Ratings and Characteristics (T <sub>C</sub> = 25 °C) <sup>b</sup> |                      |                                                                                                                         |       |       |       |      |
| Continuous Current                                                                   | I <sub>S</sub>       |                                                                                                                         |       |       | 40    | A    |
| Pulsed Current                                                                       | I <sub>SM</sub>      |                                                                                                                         |       |       | 60    |      |
| Forward Voltage <sup>a</sup>                                                         | V <sub>SD</sub>      | I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V                                                                            |       | 1     | 1.5   | V    |
| Reverse Recovery Time                                                                | t <sub>rr</sub>      | I <sub>F</sub> = 50 A, dl/dt = 100 A/μs                                                                                 |       | 115   | 170   | ns   |
| Peak Reverse Recovery Charge                                                         | I <sub>RM(REC)</sub> |                                                                                                                         |       | 7.5   | 12    | A    |
| Reverse Recovery Charge                                                              | Q <sub>rr</sub>      |                                                                                                                         |       | 0.43  | 1.02  | μC   |

Notes:

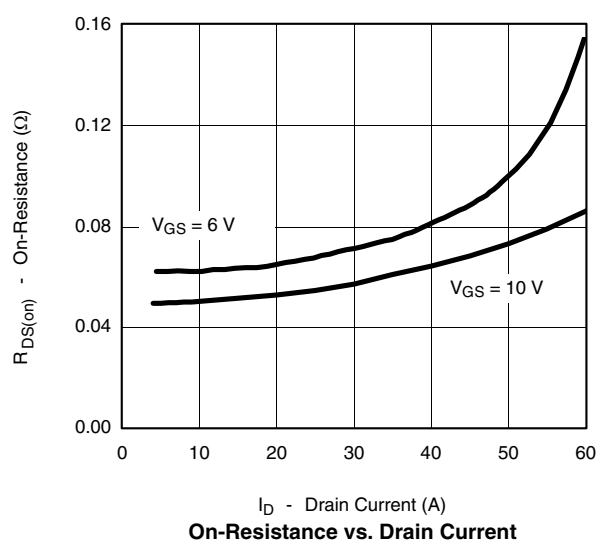
a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

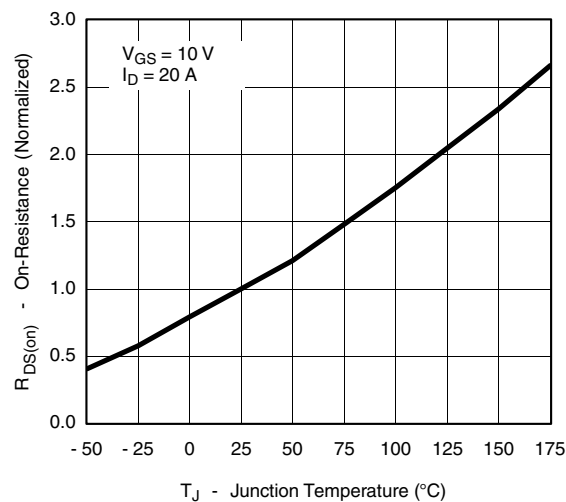
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C unless noted)



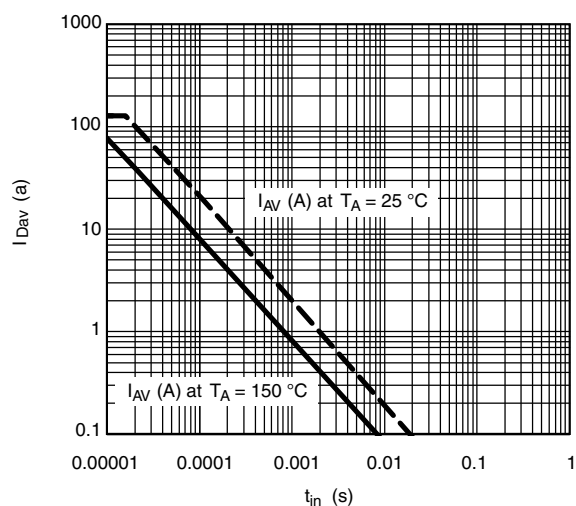
**TYPICAL CHARACTERISTICS** (25 °C unless noted)



**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



**Avalanche Current vs. Time**

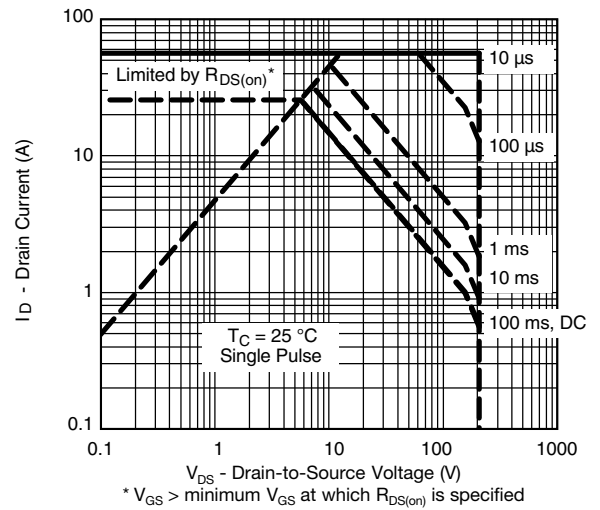


**Drain Source Breakdown vs. Junction Temperature**

## THERMAL RATINGS



**Maximum Avalanche and Drain Current  
vs. Case Temperature**



**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Case**

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